

CLAIMS

1. A voltage-controlled monolithic component of triac type, formed in a substrate (1) of a first conductivity type, including:

5 a first and a second vertical thyristor (Th1, Th2), a first main electrode (A2) of the first thyristor, on the front surface side of the component, corresponding to a first region (6) of the first conductivity type formed in a first well (5) of the second conductivity type, said first well corresponding to a first main electrode (A2) of the second thyristor, the first
10 well containing a second region (8) of the first conductivity type; and

a pilot structure including, on the front surface side, above an extension of a second main electrode region (4) of the second thyristor, a second well (11) of the second
15 conductivity type containing third and fourth regions of the first conductivity type, the third region (12) and a portion of the second well (11) being connected to a gate terminal (G), the fourth region (13) being connected to the second region (8).

2. The component of claim 1, wherein the component
20 is surrounded at its periphery with a wall of the second conductivity type (2) extending from one surface to the other of the component.

3. The component of claim 2, wherein, on the front surface side, the first well (5) includes an extension (16)
25 which surrounds the second well (11).

4. The component of claim 3, wherein the external periphery of the first well and of its extension is surrounded with a lightly-doped ring (17) of the second conductivity type.